

PSICSTAF650V20N Schoktty Barrier Diode

Feature

- Low conduction loss due to low V_F
- Extremely low switching loss by tiny Q_C
- Negligible reverse recovery
- Positive Temperature Coefficient

Uninterruptable power supplies

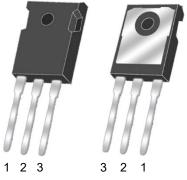
Power Factor Correction

- Pb-free / RoHS compliant
- > Highly rugged due to better surge current
- ➤ High-reliability

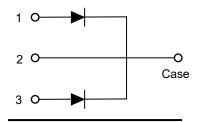
> Solar inverters

> Motor drives

Applications



TO-247-3L



Circuit Diagram

Absolute maximum rating@25°C

Parameter			Value	Units	
Repetitive Peak Reverse Voltage		V _{RRM}	650	V	
Surge Peak Reverse Voltage			650	V	
Continuous Forward Current	T _c =25°C		32*/64**	A	
	T _c =150°C	F(AVG)	10*/20**		
Non-repetitive Forward Surge Current	T _c =25°C,t _p =10ms,Half Sine Pulse	I _{FSM}	105	А	
Power Dissipation	T _c =25°C		197*	w	
	T _c =110°C	- P _{tot}	85*		
Operating junction Range	TJ	-55~+175	°C		
Storage Temperature Range	T _{STG}	-55~+175	°C		

* Per leg * * Per Device

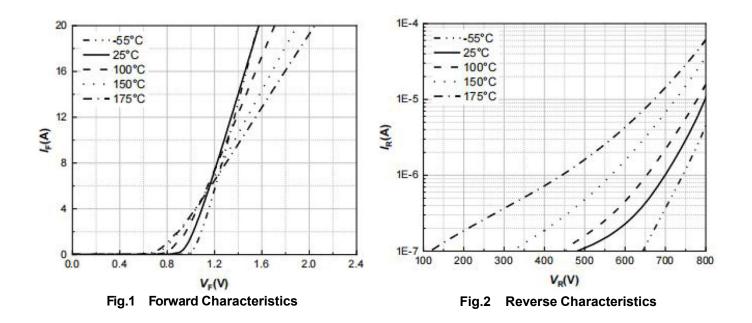
Schoktty Barrier Diode

PSICSTAF650V20N

Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
DC Blocking Voltage	V _{DC}		650	-	-	V
Forward Voltage	V _F	I _F = 10A, T _j =25°C	-	1.29	-	v
		I _F = 10A, T _j =175°C	-	1.40	-	
Reverse Current	I _R	V _R = 650V, T _j =25°C	-	1	-	μA
		V _R = 650V, T _j =175°C	-	3	-	
Total Capacitive Charge	Q _c	$V_{R} = 400V, T_{j} = 25^{\circ}C,$ $Q_{C} = \int_{0}^{V_{R}} C(V) dV$	-	38*	-	nC
Total Capacitance	С	V _R = 1V,f = 1MHz	-	551	-	pF
		V _R = 300V,f = 1MHz	-	63	-	
		V _R = 400V,f = 1MHz	-	57	-	
Capacitance stored energy	E _c	V _R = 400V	-	5.7	-	μJ

Typical Characteristics



Schoktty Barrier Diode

PSICSTAF650V20N

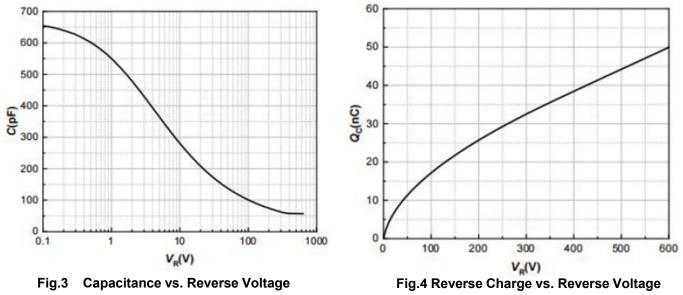
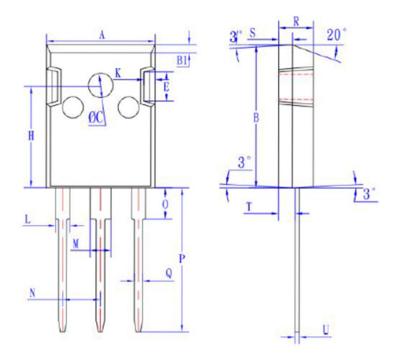


Fig.3 Capacitance vs. Reverse Voltage

Schoktty Barrier Diode

Product dimension (TO-247-3L)



Dim	Millimeters			
Dim	Min	Мах		
A	15.51	15.71		
В	20.42	20.52		
B1	0.89	1.12		
С	3.62	4.59		
E	4.15	4.25		
н	14.22	14.56		
К	1.50	1.68		
L	1.97	2.02		
м	2.95	3.10		
N	5.41	5.46		
0	4.32	4.48		
Р	20.51	20.76		
Q	1.17	1.23		
R	4.95	5.05		
S	1.98	2.04		
Т	2.35	2.41		
U	0.60	0.66		

IMPORTANT NOTICE

Prisemi[®] are registered trademarks of Prisemi Electronics Co., Ltd (Prisemi), Prisemi reserves the right to make changes without further notice to any products herein. Prisemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Prisemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in Prisemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. Prisemi does not convey any license under its patent rights nor the rights of others. The products listed in this document are designed to be used with ordinary electronic equipment or devices, Should you intend to use these products with equipment or devices which require an extremely high level of reliability and the malfunction of with would directly endanger human life (such as medical instruments, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), please be sure to consult with our sales representative in advance.

> Website: http://www.prisemi.com For additional information, please contact your local Sales Representative. ©Copyright 2009, Prisemi Electronics Prisemi[®]is a registered trademark of Prisemi Electronics. All rights are reserved.